

The listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1.-44. (Canceled)

45. (Currently Amended) A method for manufacturing a semiconductor device comprising steps of:

providing ~~a material for promoting crystallization~~ nickel to at least a part of a semiconductor film formed over a substrate;

subjecting said semiconductor film to oxygen plasma; and

crystallizing said semiconductor film after subjecting said semiconductor film to the oxygen plasma to obtain a crystalline semiconductor film.

46. (Previously Presented) A method according to claim 45, wherein said crystallizing is performed by crystallizing said semiconductor film by irradiating with one of an infrared ray and a laser light.

47. (Previously Presented) A method according to claim 45, wherein said semiconductor film is crystallized through one of a solid state and an intermediate state between the solid state and a liquid state.

48. (Previously Presented) A method according to claim 45, wherein said gate insulating film is continuously formed without exposing to the air after forming said semiconductor film.

49. (Currently Amended) A method for manufacturing a semiconductor device comprising steps of:

providing ~~a material for promoting crystallization~~ nickel to at least a part of a semiconductor film formed over a substrate;

subjecting said semiconductor film to plasma comprising oxygen and helium; and

irradiating said semiconductor film after subjecting said semiconductor film to the plasma with one of an infrared ray and a laser light.

50. (Previously Presented) A method according to claim 49, wherein said semiconductor film is crystallized through one of a solid state and an intermediate state between the solid state and a liquid state.

51. (Canceled)

52. (Currently Amended) A method for manufacturing a semiconductor device comprising steps of:

providing ~~a material for promoting crystallization~~ nickel to at least a part of a semiconductor film formed over a substrate;

subjecting said semiconductor film to oxygen plasma;

crystallizing said semiconductor film after subjecting said semiconductor film to the oxygen plasma using said material, to obtain a crystalline semiconductor film;

patterning said crystalline semiconductor film and said gate insulating film;

forming a second gate insulating film so as to cover said crystalline semiconductor film and said gate insulating film after patterning them.

53. (Previously Presented) A method according to claim 52, wherein said crystallizing is performed by crystallizing said semiconductor film by irradiating with one of an infrared ray and a laser light.

54. (Previously Presented) A method according to claim 52, wherein said semiconductor film is crystallized through one of a solid state and an intermediate state between the solid state and a liquid state.

55. (Canceled)

56. (Currently Amended) A method for manufacturing a semiconductor device comprising steps of:

providing ~~a material for promoting crystallization~~ nickel to at least a part of a semiconductor film formed over a substrate;

subjecting said semiconductor film to oxygen plasma;

irradiating said semiconductor film after subjecting said semiconductor film to the oxygen plasma with one of an infrared ray and a laser light; and

patterning said crystalline semiconductor film.

57. (Previously Presented) A method according to claim 56, further comprising a step of forming a second gate insulating film on the patterned semiconductor film.

58. (Previously Presented) A method according to claim 56, wherein said semiconductor film is crystallized through one of a solid state and an intermediate state between the solid state and a liquid state.

59. (Canceled)

60. (Currently Amended) A method for manufacturing a semiconductor device comprising steps of:

providing ~~at least one metal element~~ nickel to at least a part of a semiconductor film formed over a substrate;  
subjecting said semiconductor film to oxygen plasma;  
crystallizing said semiconductor film after subjecting said semiconductor film to the oxygen plasma to obtain a crystalline semiconductor film; and  
patterning said crystalline semiconductor film.

61. (Previously Presented) A method according to claim 60, wherein said crystallizing is performed by crystallizing said semiconductor film by irradiating with one of an infrared ray and a laser light.

62. (Previously Presented) A method according to claim 60, wherein said semiconductor film is crystallized through one of a solid state and an intermediate state between the solid state and a liquid state.

63. (Canceled)

64. (Currently Amended) A method for manufacturing a semiconductor device comprising steps of:

providing ~~at least one metal element~~ nickel to at least a part of a semiconductor film formed over a substrate;  
subjecting said semiconductor film to oxygen plasma; and  
irradiating said semiconductor film after subjecting said semiconductor film to the oxygen plasma with one of an infrared ray and a laser light.

65. (Previously Presented) A method according to claim 64, wherein said semiconductor film is crystallized through one of a solid state and an intermediate state between the solid state and a liquid state.

66.-72. (Canceled)